



General Description

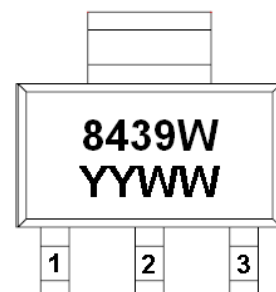
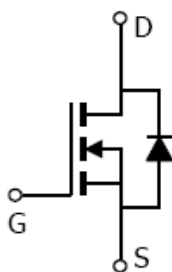
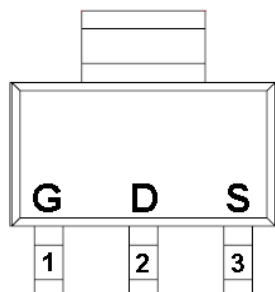
AFN8439W, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- 30V/6.0A, $R_{DS(ON)}=50m\Omega@V_{GS}=4.5V$
- 30V/5.5A, $R_{DS(ON)}=60m\Omega@V_{GS}=2.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- SOT-223 package design

Pin Description (SOT-223)



Application

- Power Management in Note book
- LED Display
- DC-DC System
- LCD Panel

Pin Define

Pin	Symbol	Description
1	G	Gate
2	D	Drain
3	S	Source

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN8439WS223RG	8439W	SOT-223	Tape & Reel	2500 EA

※ YY year code

※ WW week code

※ AFN8439WS223RG : 13" Tape & Reel ; Pb- Free ; Halogen- Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate –Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C 6.0	A
		T _A =70°C 4.8	
Pulsed Drain Current	I _{DM}	20	A
Continuous Source Current(Diode Conduction)	I _S	1.5	A
Power Dissipation	P _D	T _A =25°C 2.8	W
		T _A =70°C 1.2	
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	120	°C/W

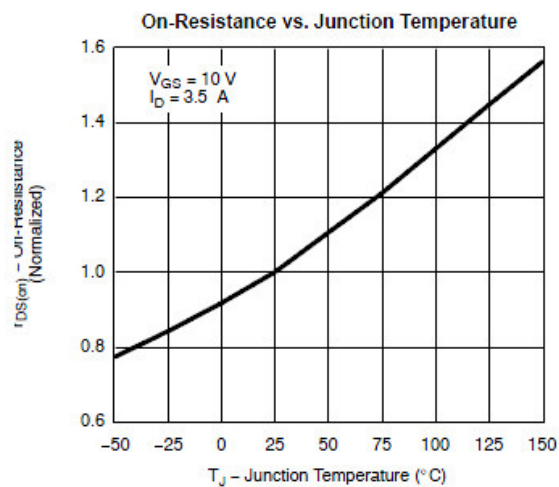
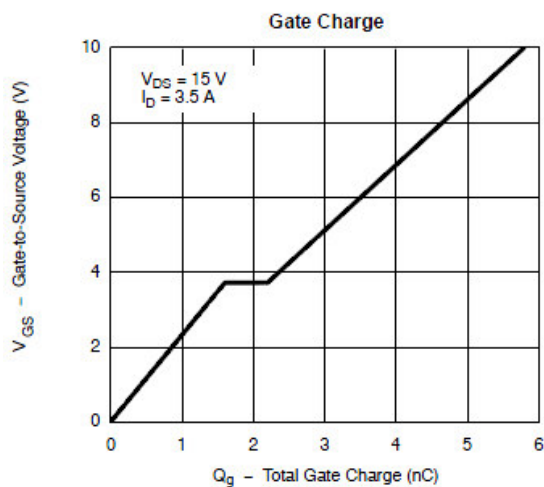
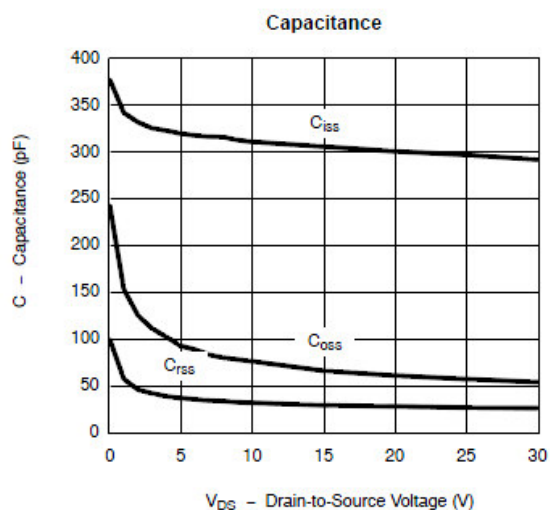
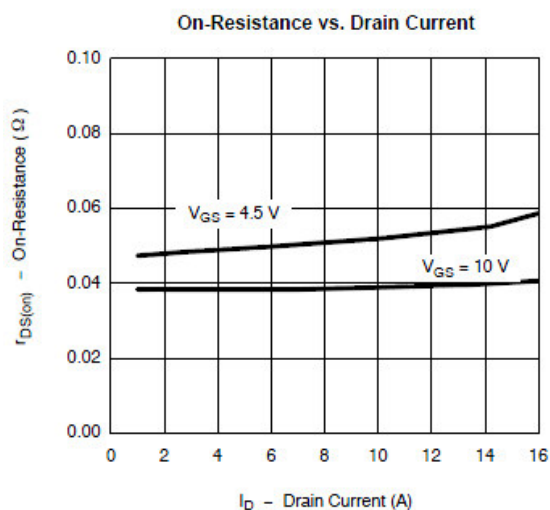
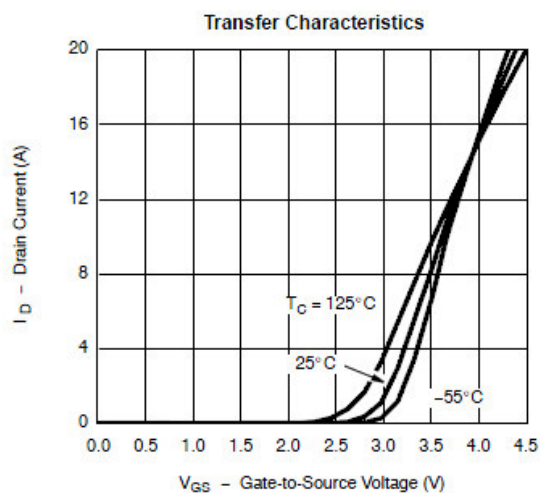
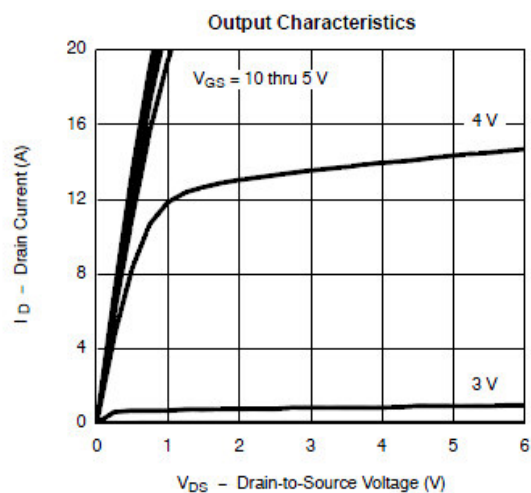
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.4		1.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	uA
		V _{DS} =24V, V _{GS} =0V			30	
		T _J =85°C				
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 4.5V, V _{GS} =10V	6			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =6.0A		39	50	mΩ
		V _{GS} =2.5V, I _D =5.5A		45	60	
Forward Transconductance	g _{FS}	V _{DS} =4.5V, I _D =2.5A		8		S
Diode Forward Voltage	V _{SD}	I _S =3.4A, V _{GS} =0V		0.8	1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =15V, V _{GS} =10V I _D ≡2.6A		3.0	4.5	nC
Gate-Source Charge	Q _{gs}			1.6		
Gate-Drain Charge	Q _{gd}			0.6		
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V f=1MHz		320		pF
Output Capacitance	C _{oss}			70		
Reverse Transfer Capacitance	C _{rss}			30		
Turn-On Time	t _{d(on)}	V _{DD} =15V, R _L =15Ω I _D ≡1.0A, V _{GEN} =10V R _G =6Ω		8	12	ns
	t _r			12	18	
Turn-Off Time	t _{d(off)}			15	30	
	t _f			8	15	

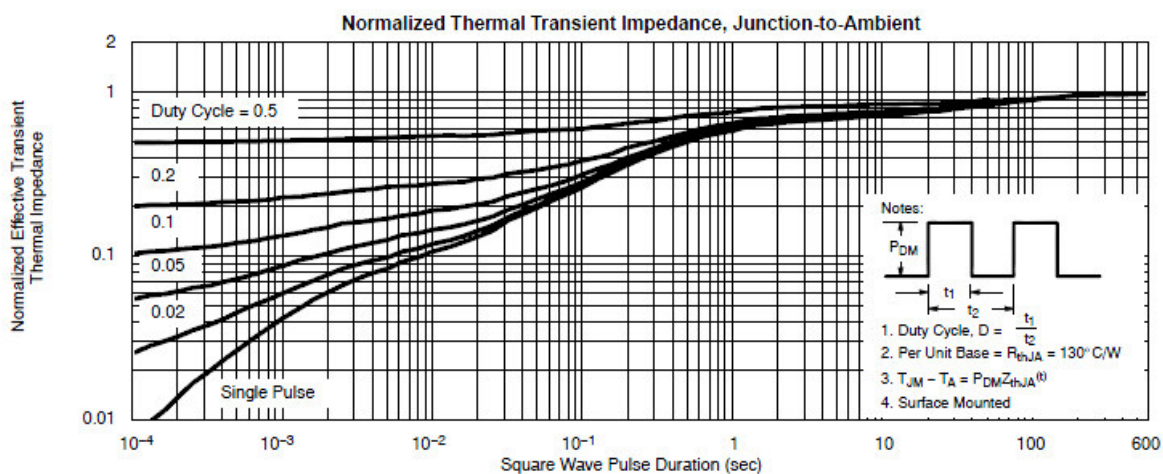
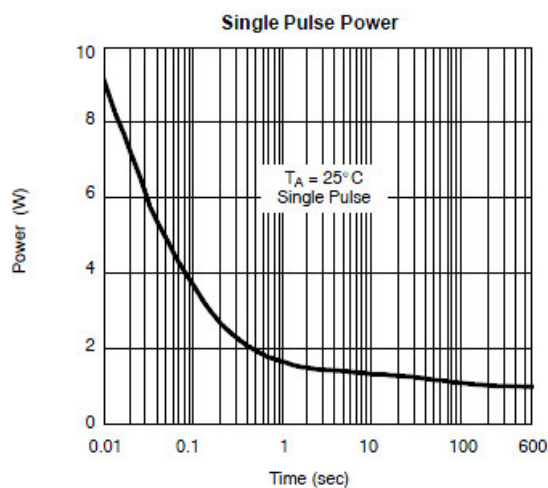
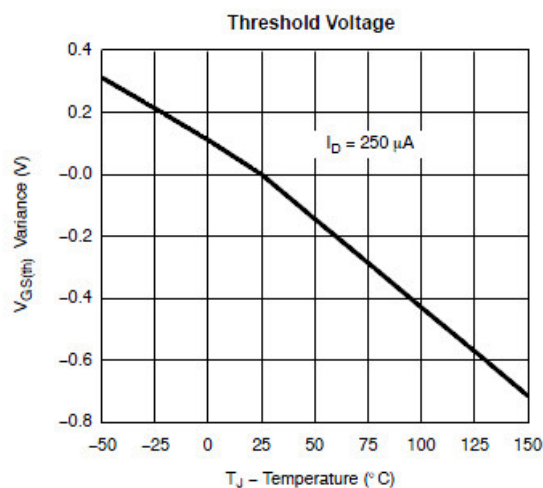
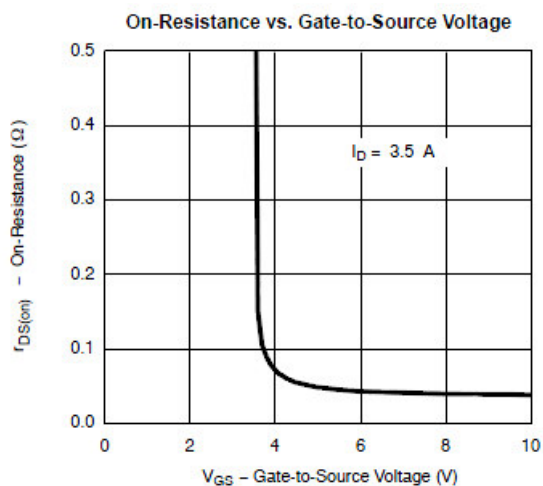
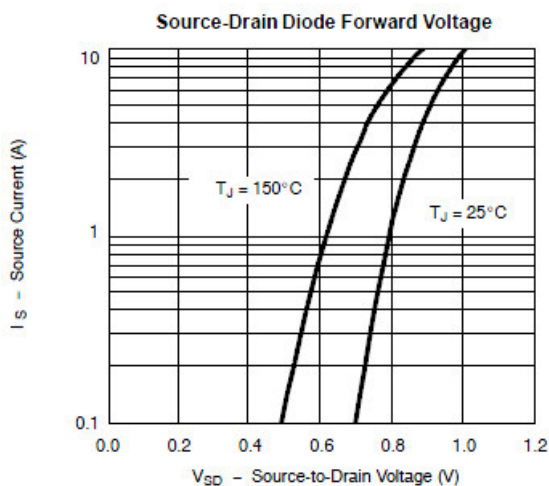


Typical Characteristics





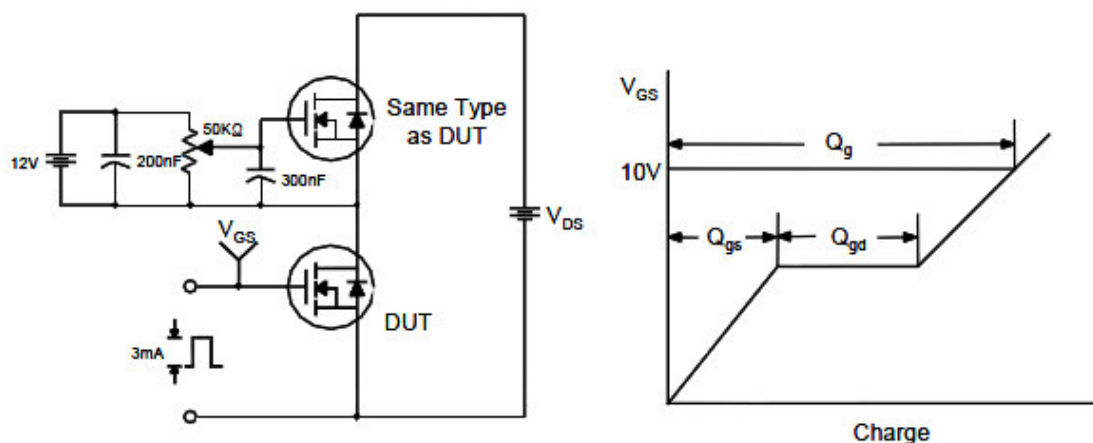
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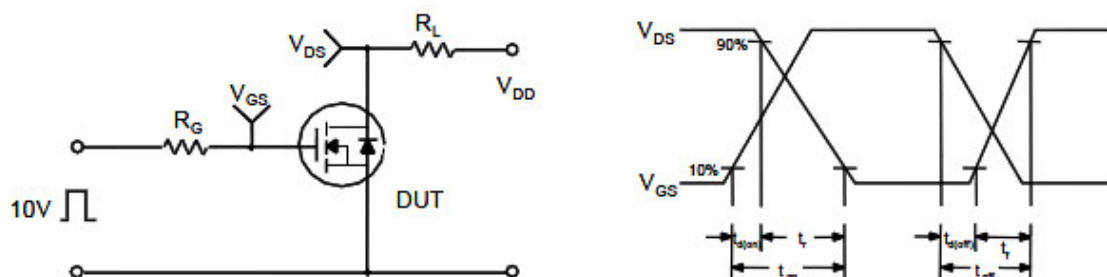


Typical Characteristics

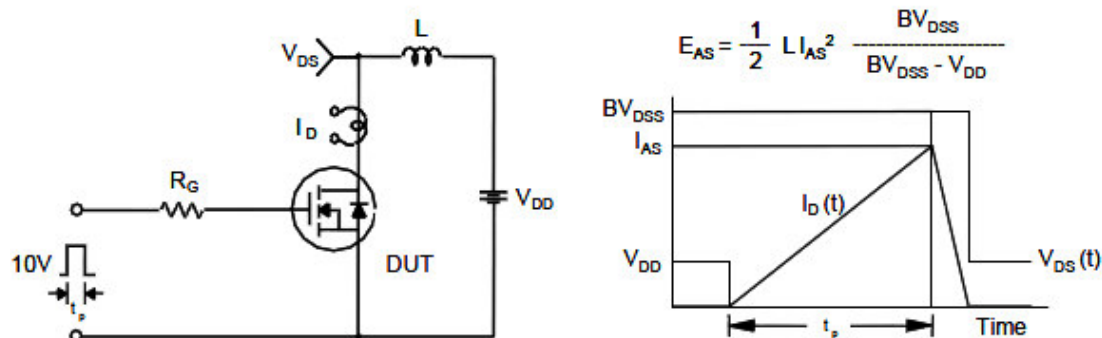
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

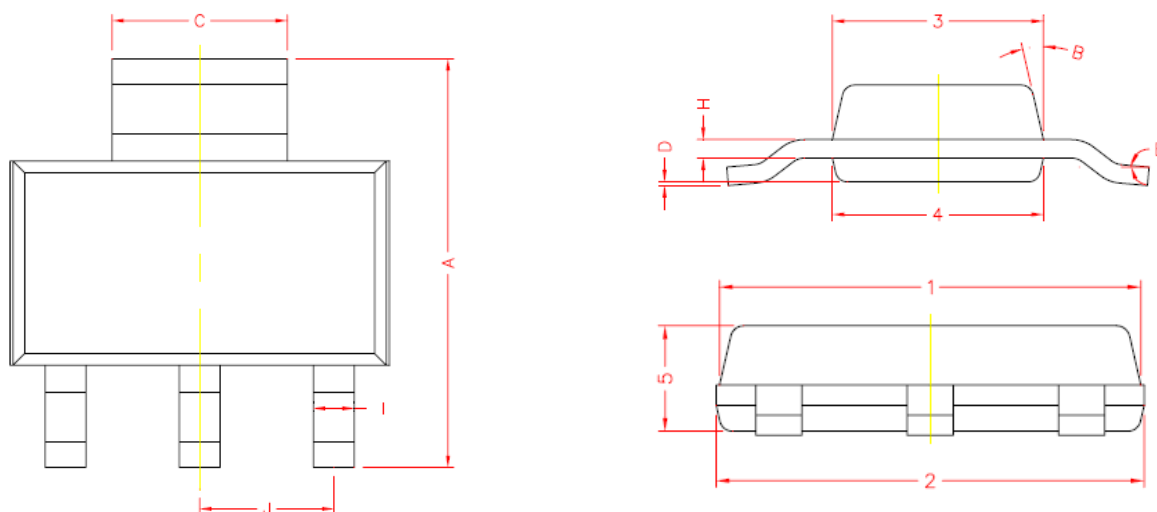


Unclamped Inductive Switching Test Circuit & Waveforms





Package Information (SOT-223)



REF.	DIMENSIONS	
	Millimeters	
	Min.	Max.
A	6.70	7.30
C	2.90	3.10
D	0.02	0.10
E	0°	10°
I	0.60	0.80
H	0.25	0.35
B	13° TYP.	
J	2.30 REF.	
1	6.30	6.70
2	6.30	6.70
3	3.30	3.70
4	3.30	3.70
5	1.40	1.80

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